

N-channel SiC power MOSFET

V_{DSS}	650V
$R_{DS(on)}$ (Typ.)	120m $Ω$
I _D	21A
P_D	103W

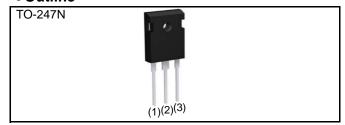
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

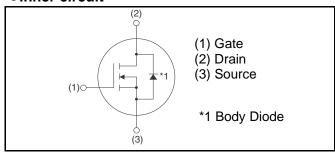
Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

Outline



●Inner circuit



Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Type	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Taping code	C11
	Marking	SCT3120AL

◆Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{ extsf{DSS}}$	650	V	
Continuous drain current	T _c = 25°C	I _D *1	21	А
Continuous drain current	T _c = 100°C	l _D *1	15	А
Pulsed drain current	I _{D,pulse} *2	52	А	
Gate - Source voltage		V_{GSS}	-4 to 22	V
Gate-Source Surge Voltage	V_{GSS_surge}	−4 to 22	V	
Recommended Drive Voltage		V_{GS_op}	0 / 18	V
Junction temperature		T _j	175	°C
Range of storage temperature	T _{stg}	-55 to +175	°C	

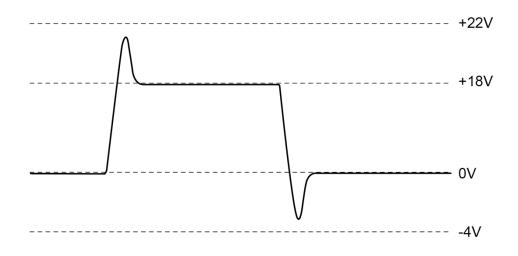
●Thermal resistance

Parameter	Symbol	Values			Unit
Parameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R _{thJC}	-	1.12	1.46	°C/W

•Electrical characteristics $(T_a = 25^{\circ}C)$

Doromotor	Cymhol	Conditions	Values			Unit
Parameter	Symbol	Symbol Conditions -		Тур.	Max.	Onit
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	650	-	-	V
		$V_{DS} = 650 \text{V}, V_{GS} = 0 \text{V}$				
Zero gate voltage drain current	I _{DSS}	$T_j = 25$ °C	-	1	10	μΑ
		T _j = 150°C	-	2	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS} _	$V_{GS} = -4V$, $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V, I_D = 3.33mA$	2.7	-	5.6	V
		$V_{GS} = 18V, I_D = 6.7A$				
Static drain - source on - state resistance	R _{DS(on)} *3	T _j = 25°C	-	120	156	mΩ
		T _j = 125°C	-	158.4	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	18	-	Ω

●Example of acceptable Vgs waveform



●Electrical characteristics (T_a = 25°C)

Doromotor	Cumbal	Symbol Conditions -		Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	g fs *3	$V_{DS} = 10V, I_D = 6.7A$	-	2.7	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	460	-	
Output capacitance	C _{oss}	V _{DS} = 500V	-	35	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	16	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 300V	-	70	•	pF
Turn - on delay time	t _{d(on)} *3	$V_{DD} = 300V, I_D = 6.7A$	-	14	-	
Rise time	t _r *3	V _{GS} = 18V/0V	-	21	-	20
Turn - off delay time	t _{d(off)} *3	$R_L = 45\Omega$	-	23	-	ns
Fall time	t _f *3	$R_G = 0\Omega$	-	14	-	
Turn - on switching loss	E _{on} *3	$V_{DD} = 300V, I_{D} = 6.7A$ $V_{GS} = 18V/0V$	-	29	-	1
Turn - off switching loss	E _{off} *3	R _G = 0Ω L=500μH *E _{on} includes diode reverse recovery	-	3	-	μJ

•Gate Charge characteristics ($T_a = 25$ °C)

Parameter	meter Symbol	Conditions	Values			Unit
raiametei			Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*3}	V _{DD} = 300V	-	38	-	
Gate - Source charge	Q _{gs} *3	$I_{D} = 6.7A$	-	11	-	nC
Gate - Drain charge	Q _{gd} *3	V _{GS} = 18V	-	13	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 300V, I_D = 6.7A$	-	9.6	1	V

^{*1} Limited only by maximum temperature allowed.

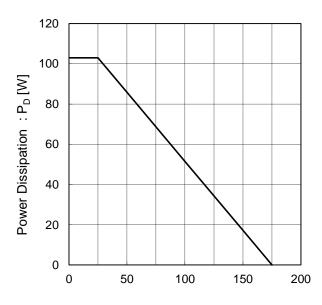
^{*2} PW \leq 10 $\mu s,$ Duty cycle \leq 1%

^{*3} Pulsed

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

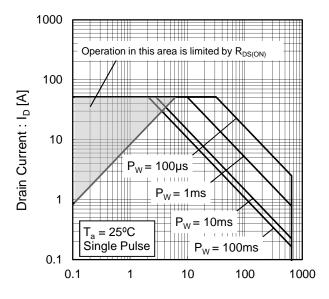
Parameter	Symbol	Conditions	Values			Unit	
r ai ai nietei	arameter Symbol Conditions		Min.	Тур.	Max.	Offic	
Inverse diode continuous, forward current	l _S *1	-T _c = 25°C	-	1	21	А	
Inverse diode direct current, pulsed	I _{SM} *2		-	-	52	А	
Forward voltage	V _{SD} *3	$V_{GS} = 0V, I_{S} = 6.7A$	-	3.2	ı	V	
Reverse recovery time	t _{rr} *3		-	13	ı	ns	
Reverse recovery charge	Q _{rr} *3	I _F = 6.7A, V _R = 300V di/dt = 1100A/μs	-	35	-	nC	
Peak reverse recovery current	I _{rrm} *3		-	6	-	Α	

Fig.1 Power Dissipation Derating Curve

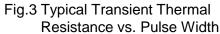


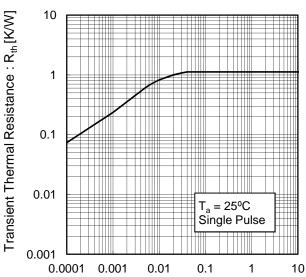
Junction Temperature : T_i [°C]

Fig.2 Maximum Safe Operating Area



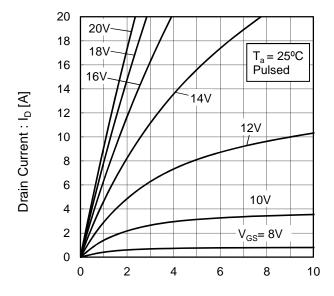
Drain - Source Voltage : V_{DS} [V]





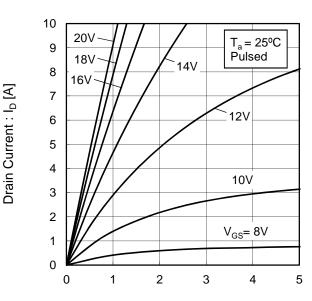
Pulse Width: P_W [s]

Fig.4 Typical Output Characteristics(I)

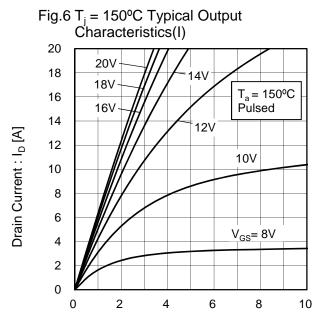


Drain - Source Voltage : V_{DS} [V]

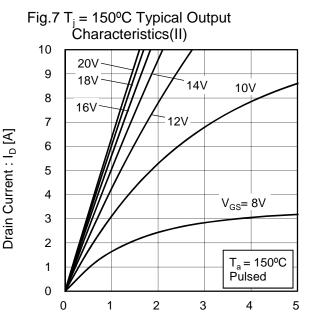
Fig.5 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]



Drain - Source Voltage : $V_{DS}[V]$



Drain - Source Voltage : V_{DS} [V]

Fig.8 Typical Transfer Characteristics (I)

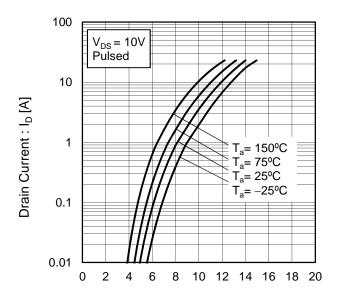
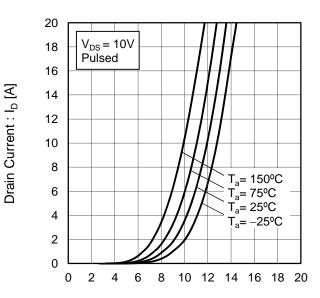


Fig.9 Typical Transfer Characteristics (II)

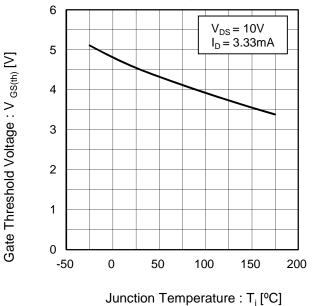


Gate - Source Voltage : V_{GS} [V]

Fig.11 Transconductance vs. Drain Current

Gate - Source Voltage : V_{GS} [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature



Transconductance : g_{fs} [S]

10 $V_{DS} = 10V$ Pulsed $T_a = 150^{\circ}C$ $T_a = 75^{\circ}C$ $T_a = 25^{\circ}C$ $T_a = -25^{\circ}C$ 0.1 0.1 1 10

Drain Current : I_D [A]

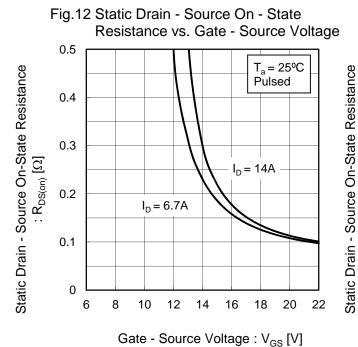
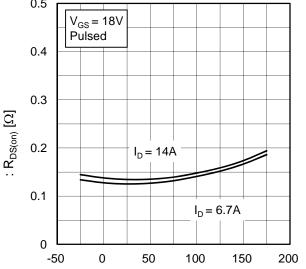
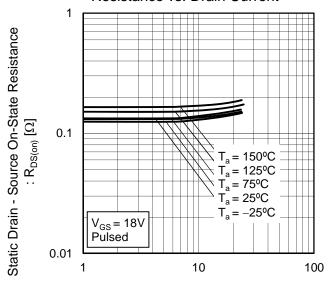


Fig.13 Static Drain - Source On - State
Resistance vs. Junction Temperature



Junction Temperature : T_i [°C]

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



Drain Current: I_D [A]

10

1

0.1

•Electrical characteristic curves

 $T_a = 25^{\circ}C$

f = 1MHz $V_{GS} = 0V$

Fig.15 Typical Capacitance vs. Drain - Source Voltage 10000 1000 Capacitance: C [pF] C_{oss} 100

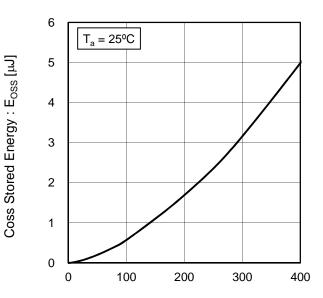
Drain - Source Voltage : V_{DS} [V]

100

1000

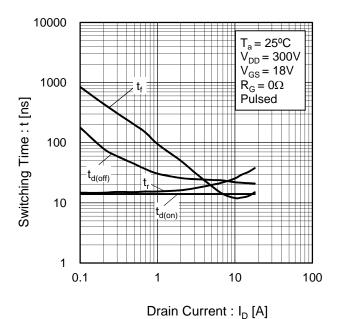
10

Fig.16 Coss Stored Energy



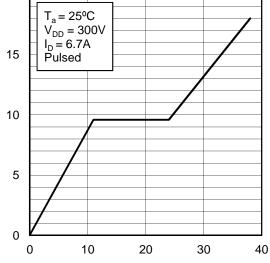
Drain - Source Voltage : V_{DS} [V]

Fig.17 Switching Characteristics



20 $T_a = 25^{\circ}C$

Fig.18 Dynamic Input Characteristics



Total Gate Charge : Q_g [nC]

3ate - Source Voltage: V_{GS} [V]

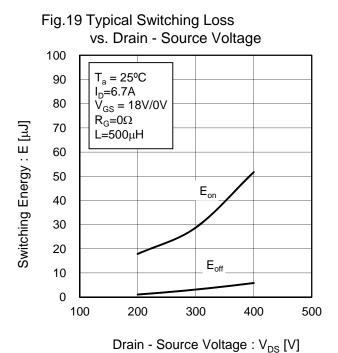
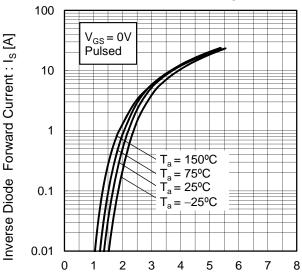


Fig.20 Typical Switching Loss vs. Drain Current 200 $T_a = 25^{\circ}C$ $V_{DD} = 300V$ $V_{GS} = 18V/0V$ $R_{G} = 0\Omega$ Switching Energy : E [µJ] 150 L=500uH 100 E_{on} 50 $\mathsf{E}_{\mathsf{off}}$ 0 0 5 10 15 20 Drain Current: I_D [A]

Fig.21 Typical Switching Loss vs. External Gate Resistance 200 $T_a = 25^{\circ}C$ V_{DD}=300V $I_{D} = 6.7A$ $V_{GS} = 18V/0V$ $L = 500 \mu H$ 150 Switching Energy: E [μJ] 100 E_{on} 50 $\mathsf{E}_{\mathsf{off}}$ 0 5 0 10 15 20 25 30

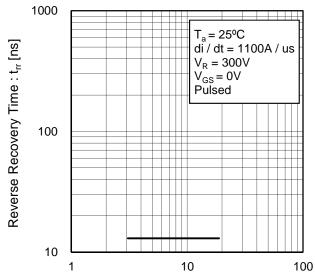
External Gate Resistance : $R_G[\Omega]$

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

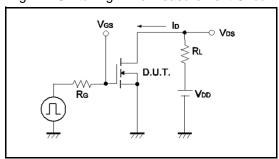


Fig.2-1 Gate Charge Measurement Circuit

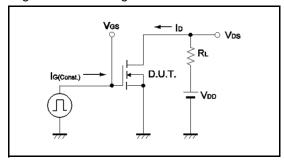


Fig.3-1 Switching Energy Measurement Circuit

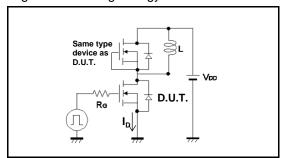


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

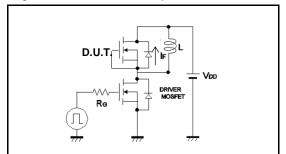


Fig.1-2 Switching Waveforms

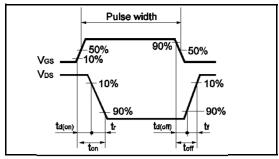


Fig.2-2 Gate Charge Waveform

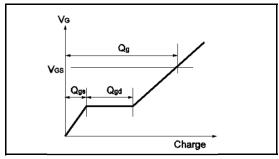
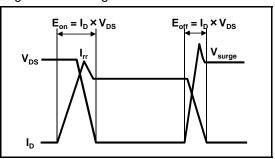
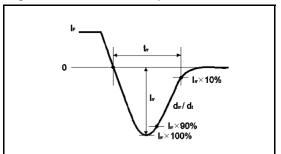


Fig.3-2 Switching Waveforms





Notes

- 1) The information contained herein is subject to change without notice.
- Before you use our Products, please contact our sales representative and verify the latest specifications:
- 3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors. Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM
- 4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.
- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
- 6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.
- 7) The Products specified in this document are not designed to be radiation tolerant.
- 8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.
- 9) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
- 10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
- 11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
- 12) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
- 13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
- 14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/



SCT3120AL - Web Page

Distribution Inventory

Part Number	SCT3120AL
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes